

L Number	Hits	Search Text	DB	Time stamp
1	5802280	(semiconductor si silicon gaas) wuth (substrate layer carrier)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:47
2	744971	mandril raised bevel beveled beveling	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:48
3	47808	((semiconductor si silicon gaas) wuth (substrate layer carrier)) with (mandril raised bevel beveled beveling)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:50
4	7615	((semiconductor si silicon gaas) wuth (substrate layer carrier)) with (mandril raised bevel beveled beveling)) and ((integrated adj circuit) ic)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:50
5	1680	perpendicular and (((semiconductor si silicon gaas) wuth (substrate layer carrier)) with (mandril raised bevel beveled beveling)) and ((integrated adj circuit) ic))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:51
6	1548	(edge end border) and (perpendicular and (((semiconductor si silicon gaas) wuth (substrate layer carrier)) with (mandril raised bevel beveled beveling)) and ((integrated adj circuit) ic)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:51
7	1392	(metal trace wiring conductor conductive) and ((edge end border) and (perpendicular and (((semiconductor si silicon gaas) wuth (substrate layer carrier)) with (mandril raised bevel beveled beveling)) and ((integrated adj circuit) ic)))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:52
8	813	(angle incline inclination inclining) and ((metal trace wiring conductor conductive) and ((edge end border) and (perpendicular and (((semiconductor si silicon gaas) wuth (substrate layer carrier)) with (mandril raised bevel beveled beveling)) and ((integrated adj circuit) ic))))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/09/27 17:53
9	1089	(degree angle incline inclination inclining) and ((metal trace wiring conductor conductive) and ((edge end border) and (perpendicular and (((semiconductor si silicon gaas) wuth (substrate layer carrier)) with (mandril raised bevel beveled beveling)) and ((integrated adj circuit) ic))))	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/27 17:54